Supporting Information

Interpenetrating polymer network dielectrics for high-performance organic field-effect transistors

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Figure S1. DSC thermograms of the PMMA, PMMA90/PhSSQZ10, PMMA80/PhSSQZ20, and PMMA70/PhSSQZ30

Figure S2. Current density-electric field ($J$ vs. $E$) characteristics of the PMMA-q annealed at different conditions.
Figure S3. Output characteristics of OFETs based on the IPN gate dielectrics. The gate voltage was varied between 0 and -40 V in steps of -10 V.

Figure S4. Output and transfer characteristics of OFETs based on the 78.3 nm-thick PMMA-q gate dielectrics; drain current (closed circle) and gate current (open circle).

Figure S5. AFM topography of the 50 nm-thick pentacene films deposited on the pristine gate dielectrics (PMMA, PtBMA, and PS).